

PRODUCT RELIABILITY REPORT FOR

MAXQ2000 Rev A3

Dallas Semiconductor

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Prepared by:

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Conclusion

The following qualification successfully meets the quality and reliability standards required of all Dallas Semiconductor products:

MAXQ2000 Rev A3

In addition, Dallas Semiconductor's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

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AfT = \exp((Ea/k)^*(1/Tu - 1/Ts)) = tu/ts
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AfT = Acceleration factor due to Temperature

tu = Time at use temperature (e.g. 55°C)

ts = Time at stress temperature (e.g. 125°C)

k = Boltzmann's Constant (8.617 x 10-5 eV/°K)

Tu = Temperature at Use (°K)

Ts = Temperature at Stress (°K)

Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

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AfV = exp(B*(Vs - Vu))
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AfV = Acceleration factor due to Voltage

Vs = Stress Voltage (e.g. 7.0 volts)

Vu = Maximum Operating Voltage (e.g. 5.5 volts)

B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

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Fr = X/(ts * AfV * AfT * N * 2)
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X = Chi-Sq statistical upper limit

N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE: MTTF (YRS): 23383 FITS: 4.9

The parameters used to calculate this failure rate are as follows:

Cf: 60% Ea: 0.7 B: 0 Tu: 25 °C Vu: 5.5 Volt

The reliability data follows. A the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. "*" after DATE CODE denotes specific product

Device Information:

Process:

Passivation: OxyNit LaserNoA&E - Pass/Nov.TEOS/OxyNit -Gen.LaserP

Die Size: 104 x 124 Number of Transistors: 716300

Interconnect: Aluminum / 1% Silicon / 0.5% Copper

Gate Oxide Thickness:

ELECTRICAL CHARA	ELECTRICAL CHARACTERIZATION							
DESCRIPTION	DATE COD	CONDITION	REA	DPOINT	QTY	FAILS	FA#	
ESD SENSITIVITY	0428	EOS/ESD S5.1 HBM 500 VOLTS	1	PUL'S	3	0		
ESD SENSITIVITY	0428	EOS/ESD S5.1 HBM 1000 VOLTS	1	PUL'S	3	0		
ESD SENSITIVITY	0428	EOS/ESD S5.1 HBM 2000 VOLTS	1	PUL'S	3	3	No FA	
ESD SENSITIVITY	0428	EOS/ESD S5.1 HBM 4000 VOLTS	1	PUL'S	3	3	No FA	
ESD SENSITIVITY	0428	EOS/ESD S5.1 HBM 8000 VOLTS	1	PUL'S	3	3	No FA	
LATCH-UP	0428	JESD78, I-TEST 125C	2	DYS	6	0		
LATCH-UP	0428	JESD78, V-SUPPLY TEST 125C	2	DYS	6	0		
ESD SENSITIVITY	0540 *	EOS/ESD S5.1 HBM 500 VOLTS	1	PUL'S	3	0		
ESD SENSITIVITY	0540 *	EOS/ESD S5.1 HBM 1000 VOLTS	1	PUL'S	3	0		
ESD SENSITIVITY	0540 *	EOS/ESD S5.1 HBM 2000 VOLTS	1	PUL'S	3	3	No FA	
ESD SENSITIVITY	0540 *	EOS/ESD S5.1 HBM 1500 VOLTS	1	PUL'S	3	3	No FA	
ESD SENSITIVITY	0540 *	EOS/ESD S5.1 HBM 3000 VOLTS	1	PUL'S	3	3	No FA	
LATCH-UP	0540 *	JESD78, I-TEST 125C	2	DYS	6	0		
LATCH-UP	0540 *	JESD78, V-SUPPLY TEST 125C	2	DYS	6	0		
				Total:		18		

OPERATING LIFE						
DESCRIPTION	DATE COD	CONDITION	READPOINT	QTY	FAILS	FA
HIGH TEMP OP LIFE	0430	125C, 3.6V (PSA) & 2.75V (PSB)	1000 HRS	45	0	
HIGH TEMP OP LIFE	0506	125C, 3.6V (PSA) & 2.75V (PSB)	1000 HRS	77	0	
HIGH TEMP OP LIFE	0540 *	125C, 3.6V (PSA) & 2.75V (PSB)	1000 HRS	77	0	
			Total:		0	
W/E ENDURANCE AI	ND DATA RET	'N				
DESCRIPTION	DATE COD	CONDITION	READPOINT	QTY	FAILS	FA#
WRITE CYCLE STRESS (KCYS)	0430	85 C, 3.6V (PSA) & 2.75V (PSB)	10 KCYS	77	0	
STORAGE LIFE		150C	1000 HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0506	85 C, 3.6V (PSA) & 2.75V (PSB)	10 KCYS	77	0	
STORAGE LIFE		150C	1000 HRS	77	0	
WRITE CYCLE	0540 *	85 C, 3.6V (PSA) & 2.75V (PSB)	10 KCYS	77	0	
STRESS (KCYS)						
	*	150C	1000 HRS	76	0	